



ADAMAS UNIVERSITY
END-SEMESTER EXAMINATION : JANUARY 2021
(Academic Session: 2020 – 21)

Name of the Program:	B.TECH	Semester:	III
Paper Title :	ELECTRONIC DEVICES	Paper Code:	EEC42101
Maximum Marks :	40	Time duration:	3 hours
Total No of questions:	08	Total No of Pages:	02
Note:	<ol style="list-style-type: none">1. All parts of a Question should be answered consecutively.2. Each Answer should start from a fresh page.3. Assumptions made if any, should be stated clearly at the beginning of your answer.4. Submit scan copy of the answers on A4 sheet.		

Answer all the Groups

Group A

Answer all the questions of the following

$5 \times 1 = 5$

1.
 - a) What do you understand by compensated semiconductor??
 - b) Briefly explain the base width modulation of a BJT.
 - c) How to calculate the overall gain of a Multi-stage Amplifier?
 - d) Explain with suitable diagram n-MOSFET.
 - e) How to find out the efficiency of a solar cell?

GROUP –B

Answer *any three* of the following

$3 \times 5 = 15$

2. Design and briefly explain the input and output characteristics of an amplifier operated in Common Base (CB) configurations.
3. Write down the working principle of a PIN photo diode.
4. Design a Direct Coupled Amplifier using transistor and also explain the class of its operation.
5. A Si p-n junction diode with doping concentration in p and n region $3 \times 10^{17} \text{ cm}^{-3}$ and 10^{15} cm^{-3} respectively is in equilibrium. Calculate the contact potential for it at room temperature.

GROUP –C

Answer *any two* of the following

$2 \times 10 = 20$

6. a) Draw and explain the working principle of an EMOSFET.
b) Explain working principle of CMOS inverter. [5+5]
7. a) Draw and explain the working principle of Schottky barrier.
b) Derive the mathematical expression of depletion width in a $p^+ - n$ junction diode. [4+6]
8. a) Derive the one dimensional continuity equation for transport carriers in a semiconductor.
b) Design a Class AB amplifier and explain the working principle of it. [7+3]
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